

Impedance analysis of perovskite solar cells: a case study

Lidia Contreras-Bernal^{a,†}, Susana Ramos-Terrón^{a,†}, Antonio Riquelme^a, Pablo Boix^c, Jesús Idígoras^{a,*}, Iván Mora-Seró^{b,*}, Juan A. Anta^{a,*}

^a Área de Química Física, Universidad Pablo de Olavide, Seville, Spain.

^b Institute of Advanced Materials (INAM), Universitat Jaume I, E-12006 Castelló, Spain

^c Instituto de Ciencia Molecular, Universidad de Valencia, C/J. Beltrán 2, Paterna, Spain

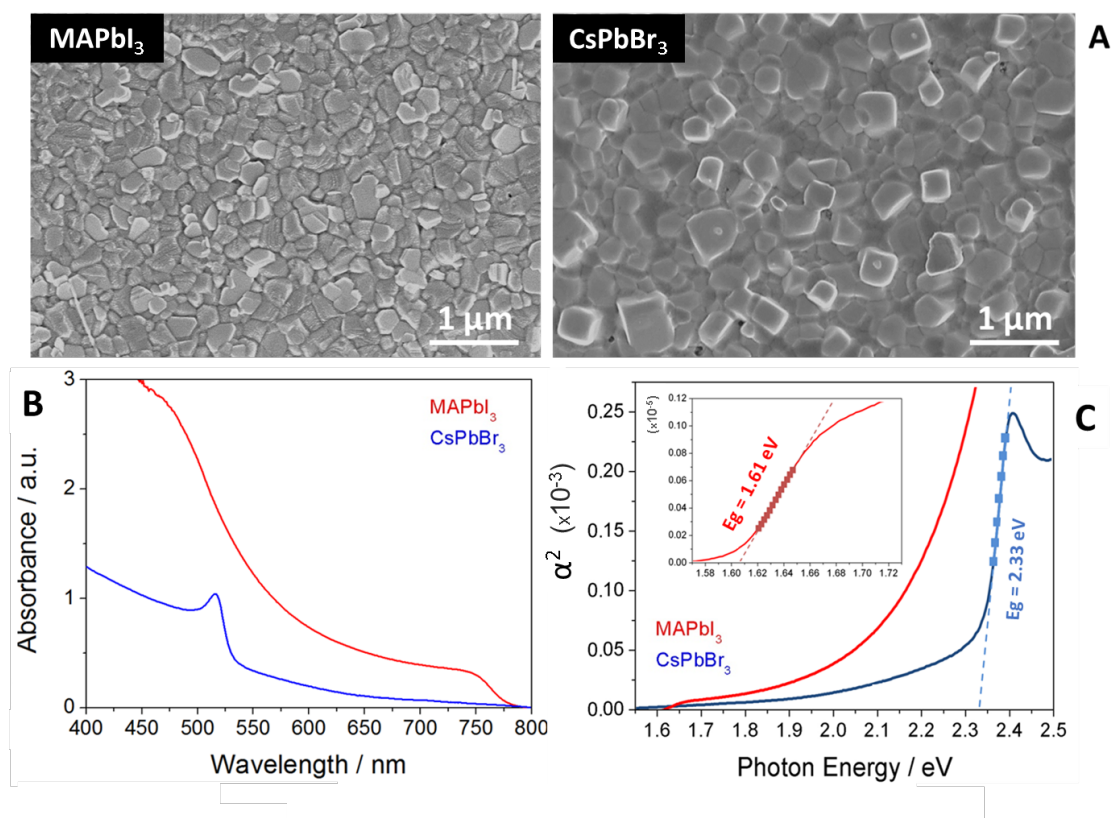


Figure S1. Morphological, and optical characterization of MAPbI_3 and CsPbBr_3 films and solar cells: (A) Plane-view scanning electron microscope images (SEM), (B) UV-Vis spectra (C) Tauc plot

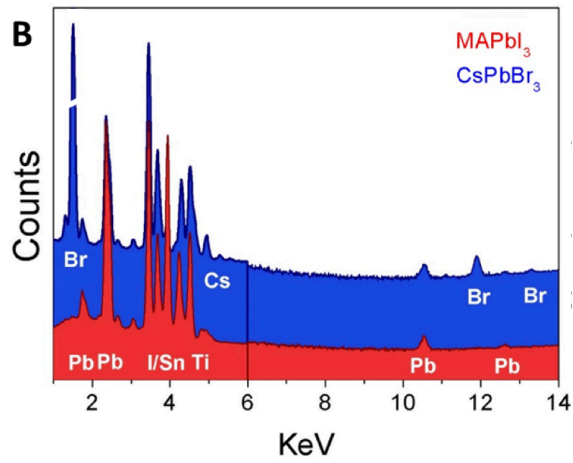


Figure S2. EDX map of MAPbI₃ and CsPbBr₃ films.

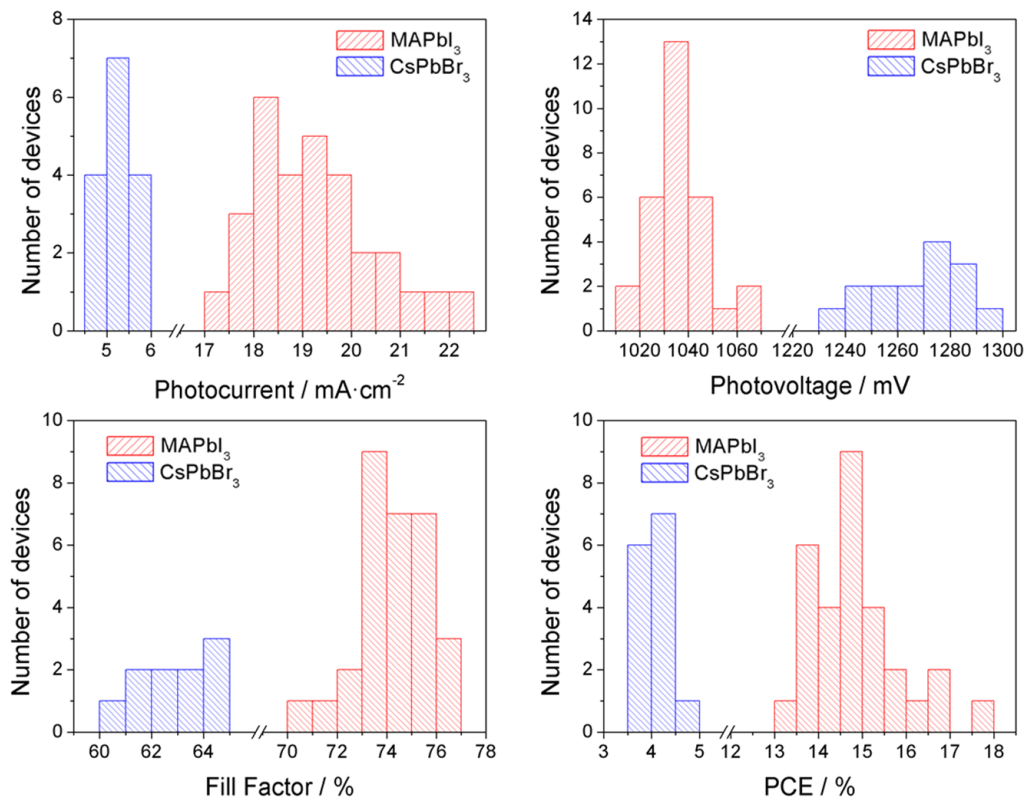


Figure S3. Statistical data of photovoltaic parameters for MAPbI₃ and CsPbBr₃ solar cell devices.

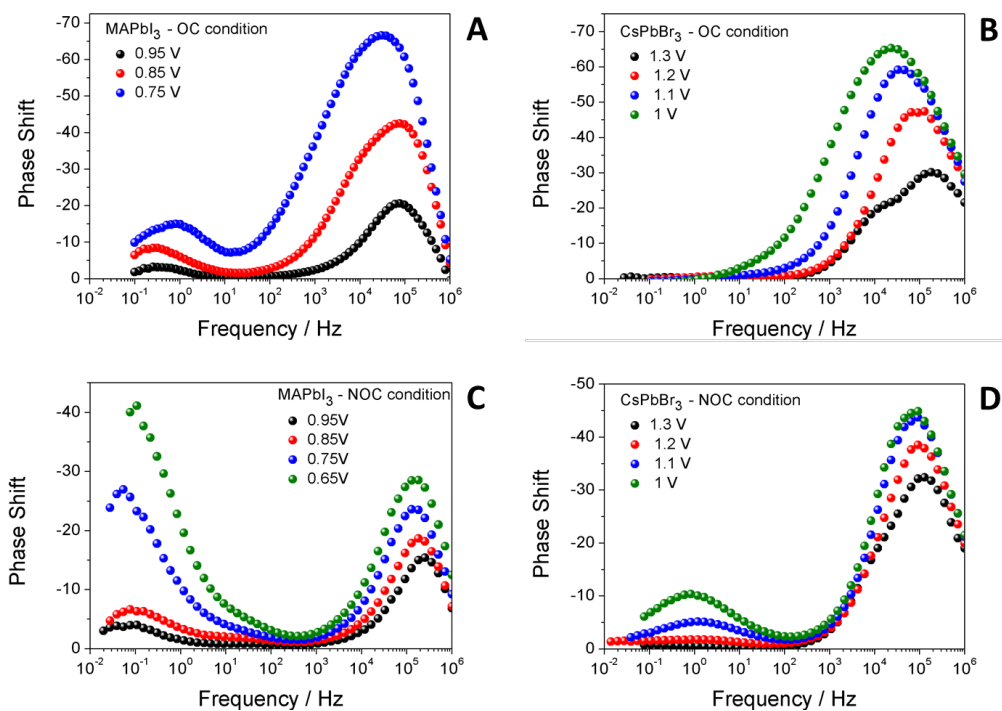


Figure S4. Impedance Bode plots of MAPbI₃ and CsPbBr₃ solar cells at OC and NOC conditions

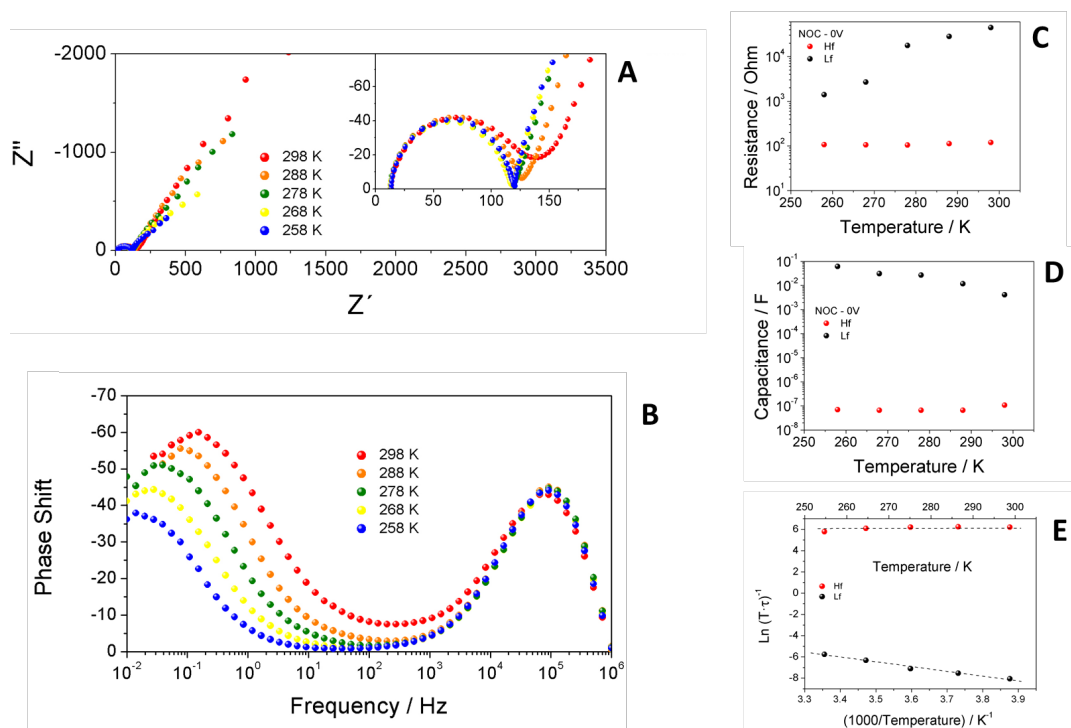


Figure S5. (A) Impedance spectra and (B) frequency plot for MAPbI₃ based devices at SC conditions and different temperatures. (C) and (D) resistances and capacitances at SC circuit as a function of temperature. (E) Arrhenius plot of the low and high frequency time constants. An activation energy of 36.9 kJ/mol can be extracted from the low frequency data.

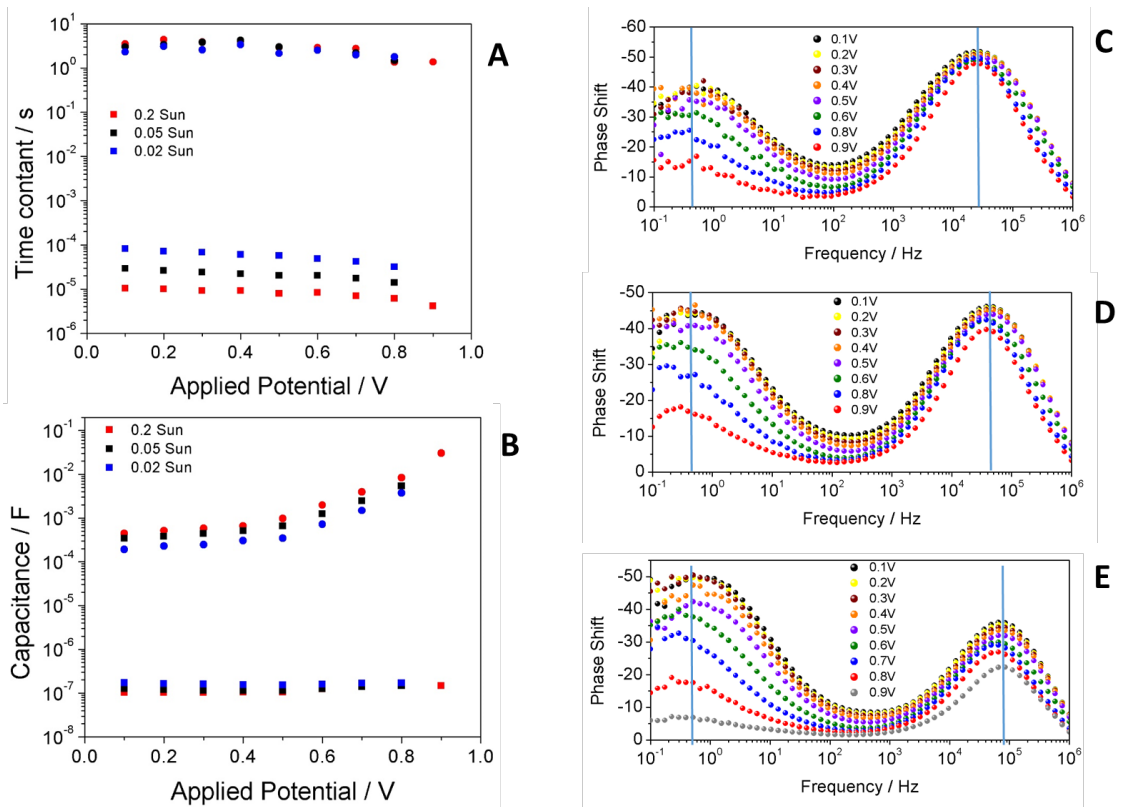


Figure S6. Effect of illumination on the impedance response of MAPbI₃ based devices at NOC conditions. In Panels (A) and (B) the voltage dependence of both the high and low frequency time constants and capacitances is shown. Frequency Bode plots at 0.02, 0.05 and 0.2 suns are shown in panels (C), (D) and (E) respectively. Vertical lines mark the position of the frequency peaks.

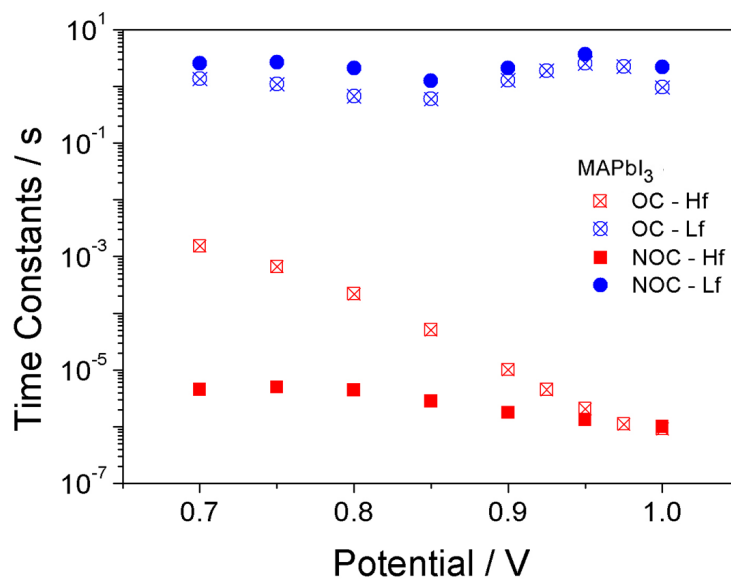


Figure S7. High and low frequency time constants as extracted from fittings for MAPbI₃ based devices at OC and NOC conditions

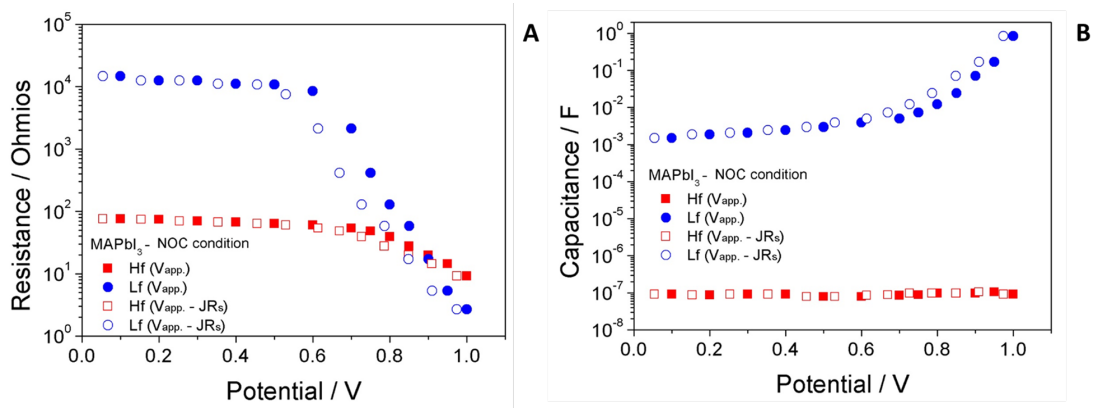


Figure S8. Correction for voltage drop due to series resistance in the impedance measurements at NOC conditions for MAPbI₃ devices.

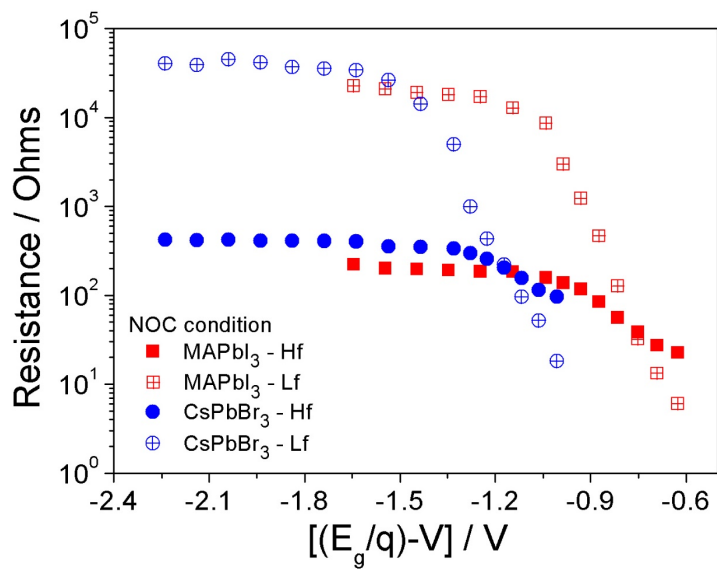


Figure S9. Resistances at NOC conditions corrected for the optical band gap of the perovskite.

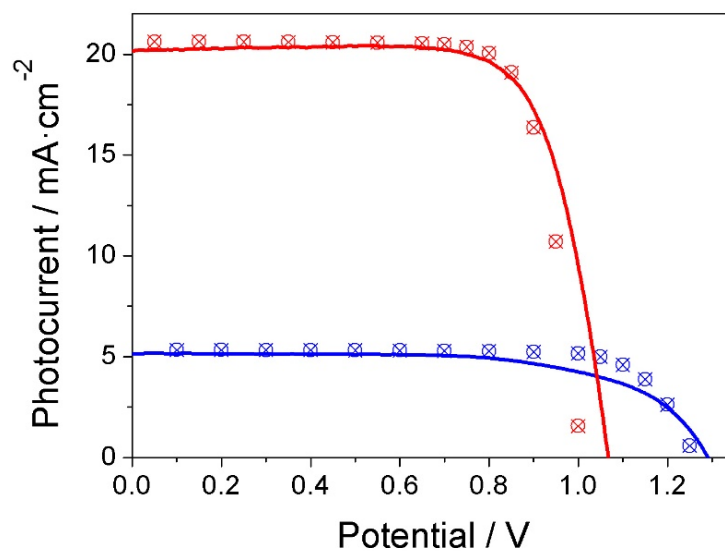


Figure S10. Experimental JV curves (symbols) and reconstruction from the impedance data at NOC conditions using Eq. (8) in the main text (lines)

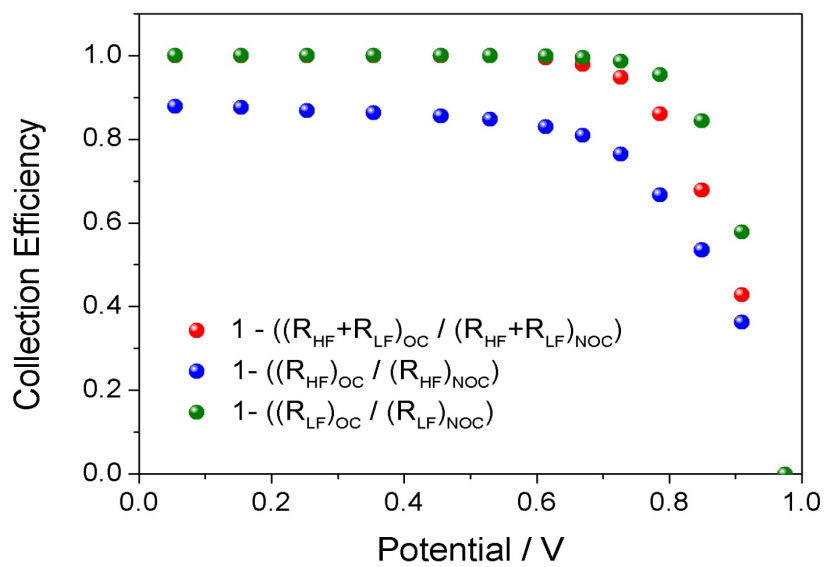


Figure S11. Charge collection efficiency of MAPbI₃ solar cells as predicted by Eq. (9) using impedance data at OC and NOC conditions for several choices of R_{rec} .

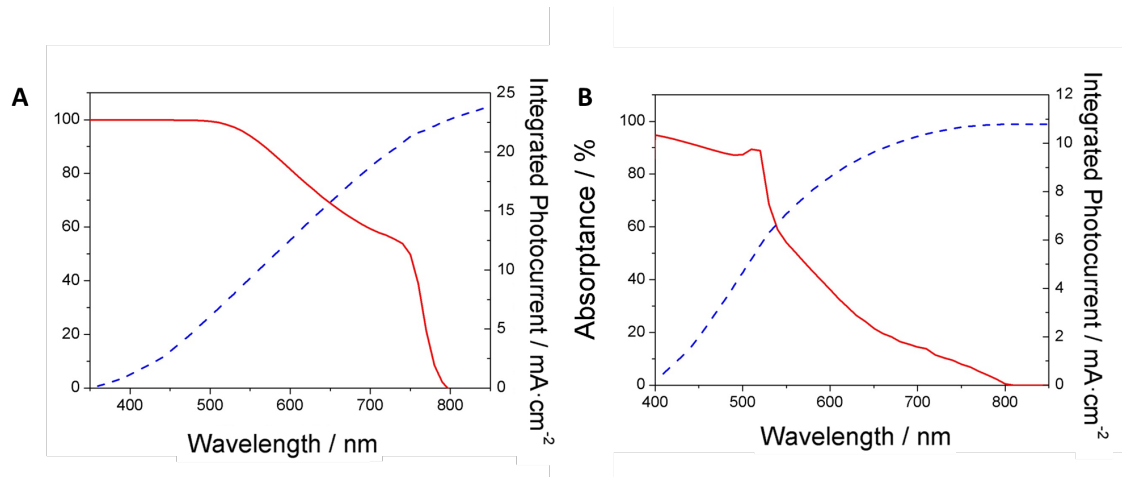


Figure S12. Absorbance and integrated photocurrent for MAPbI₃ (A) and CsPbBr₃ (B). Total integrated photocurrent amounts to 24.9 and 10.8 mA/cm², respectively.